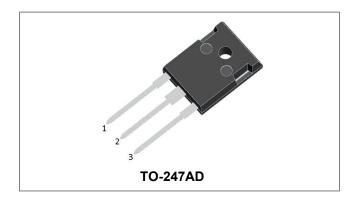






# **40CPQ200 SCHOTTKY RECTIFIER**



#### **Features**

- 175 °C T<sub>J</sub> operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- · Additional testing can be offered upon request

## **Circuit Diagram**



### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### **Maximum Ratings:**

Characteristics	stics Symbol Condition		Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage	$V_{RRM} \ V_{RWM}$	-	200	V
DC Blocking Voltage	V <sub>R</sub>			
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @Tc=145°C, rectangular wave form	20(Per Leg) 40(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I <sub>FSM</sub>	8.3ms, Half Sine pulse, T <sub>C</sub> = 25 °C	432	Α

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop	V <sub>F1</sub>	@ 20A, Pulse, T <sub>J</sub> = 25 °C	0.80	0.90	V
(Per Leg)*	$V_{F2}$	@ 20A, Pulse, T <sub>J</sub> = 125 °C	0.63	0.74	V
Reverse Current	I <sub>R1</sub>	$@V_R = \text{rated } V_{R,} T_J = 25  ^{\circ}\text{C}$	0.0003	1.5	mA
(Per Leg)*	I <sub>R2</sub>	$@V_R = \text{rated } V_{R,} T_J = 125  ^{\circ}\text{C}$	0.3	15.0	mA
Junction Capacitance(Per Leg)	Ст	$@V_R = 5V, T_C = 25  ^{\circ}C, f_{SIG} = 1MHz$	500	600	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

 $<sup>^{*}</sup>$  Pulse width < 300  $\mu$ s, duty cycle < 2%





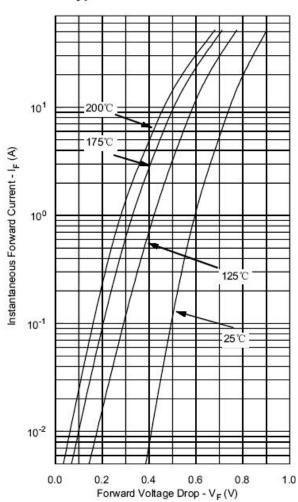


### **Thermal-Mechanical Specifications:**

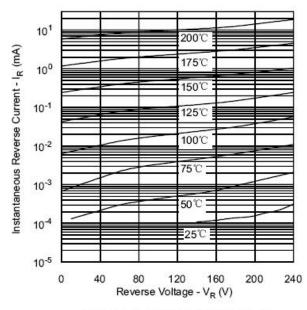
Characteristics	Symbol	Condition	Specification	Units	
Junction Temperature	TJ	-	-55 to +175	°C	
Storage Temperature	T <sub>stg</sub>	-	-55 to +175	°C	
Typical Thermal Resistance Junction to	В.	DC operation	0.63 (per leg)	°C/W	
Case	$R_{ heta JC}$	DC operation	0.31 (per device)	C/VV	
Typical Thermal Resistance, case to Heat Sink	$R_{ heta cs}$	Mounting surface, smooth and greased	0.24	°C/W	
Approximate Weight	wt	-	6.28	g	
Case Style	TO-247AD				

## **Ratings and Characteristics Curves**

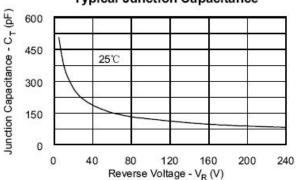
#### **Typical Forward Characteristics**



### Typical Reverse Characteristics



#### **Typical Junction Capacitance**



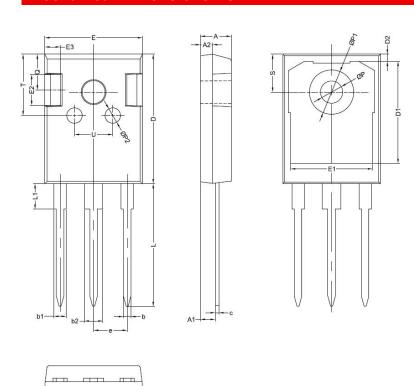
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#### **Mechanical Dimensions TO-247AD**



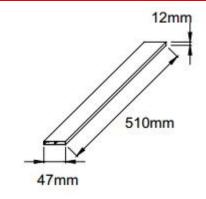
OVMDOL	Millimeters			
SYMBOL	MIN.	TYP.	MAX.	
Α	4.80	5.00	5.20	
A1	2.20	2.41	2.61	
A2	1.90	2.00	2.10	
b	1.10	1.20	1.40	
b1	1.80	2.00	2.20	
b2	2.80	3.00	3.20	
С	0.50	0.60	0.75	
D	20.30	21.00	21.20	
D1		16.55		
D2 E		1.20		
Ш	15.45	15.80	16.00	
E1		13.30		
E2		5.00		
E3		2.50		
е		5.44		
L	19.42	19.92	20.70	
L1		4.13		
Р	3.50	3.60	3.70	
P1	7.1		7.40	
P2		2.50		
Q		5.80		
Q S	6.05	6.15	6.25	
T		10.00		
U		6.20		

## **Ordering Information:**

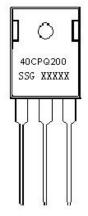
Device	Package	Shipping
40CPQ200	TO-247AD(Pb-Free)	25pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

## **Tube Specification**



## **Marking Diagram**



#### Where XXXXX is YYWWL

40 = Forward Current (40A)
C = Configuration
PQ = Device Type

PQ = Device Type 200 = Reverse Voltage (200V) SSG = SSG

YY = Year WW = Week L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

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